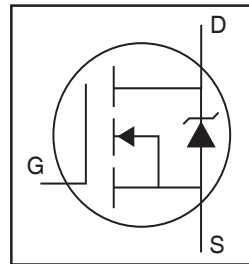


AUIRFS3006

HEXFET® Power MOSFET

Features

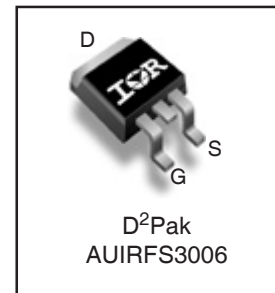
- Advanced Process Technology
- Ultra Low On-Resistance
- Dynamic dv/dt Rating
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *



| | | |
|-------------------------|------|---------------|
| V_{DSS} | | 60V |
| $R_{DS(on)}$ | typ. | 2.0mΩ |
| | max. | 2.5mΩ |
| I_D (Silicon Limited) | | 270A ① |
| I_D (Package Limited) | | 195A |

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.



| | | |
|----------|----------|----------|
| G | D | S |
| Gate | Drain | Source |

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

| Symbol | Parameter | Max. | Units |
|---------------------------------|---|---------------------------|-------|
| $I_D @ T_C = 25^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited) | 270① | A |
| $I_D @ T_C = 100^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited) | 191① | |
| $I_D @ T_C = 25^\circ\text{C}$ | Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Wire Bond Limited) | 195 | |
| I_{DM} | Pulsed Drain Current ② | 1080 | |
| $P_D @ T_C = 25^\circ\text{C}$ | Maximum Power Dissipation | 375 | W |
| | Linear Derating Factor | 2.5 | W/°C |
| V_{GS} | Gate-to-Source Voltage | ± 20 | V |
| E_{AS} | Single Pulse Avalanche Energy (Thermally Limited) ③ | 320 | mJ |
| I_{AR} | Avalanche Current ② | See Fig. 14, 15, 22a, 22b | A |
| E_{AR} | Repetitive Avalanche Energy ② | | mJ |
| dv/dt | Peak Diode Recovery ④ | 10 | V/ns |
| T_J T_{STG} | Operating Junction and Storage Temperature Range | -55 to + 175 | °C |
| | Soldering Temperature, for 10 seconds (1.6mm from case) | 300 | |
| | Mounting torque, 6-32 or M3 screw | 10lbf·in (1.1N·m) | |

Thermal Resistance

| Symbol | Parameter | Typ. | Max. | Units |
|-----------------|-----------------------|------|------|-------|
| $R_{\theta JC}$ | Junction-to-Case ⑨⑩ | — | 0.4 | °C/W |
| $R_{\theta JA}$ | Junction-to-Ambient ⑧ | — | 40 | |

HEXFET® is a registered trademark of International Rectifier.

*Qualification standards can be found at <http://www.irf.com/>

Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

| Symbol | Parameter | Min. | Typ. | Max. | Units | Conditions |
|--------------------------------------|--------------------------------------|------|------|------|-------|---|
| V _{(BR)DSS} | Drain-to-Source Breakdown Voltage | 60 | — | — | V | V _{GS} = 0V, I _D = 250μA |
| ΔV _{(BR)DSS/ΔT_J} | Breakdown Voltage Temp. Coefficient | — | 0.07 | — | V/°C | Reference to 25°C, I _D = 5mA② |
| R _{DS(on)} | Static Drain-to-Source On-Resistance | — | 2.0 | 2.5 | mΩ | V _{GS} = 10V, I _D = 170A ⑤ |
| V _{GS(th)} | Gate Threshold Voltage | 2.0 | — | 4.0 | V | V _{DS} = V _{GS} , I _D = 250μA |
| g _{fs} | Forward Transconductance | 280 | — | — | S | V _{DS} = 25V, I _D = 170A |
| R _G | Internal Gate Resistance | — | 2.0 | — | Ω | |
| I _{DSS} | Drain-to-Source Leakage Current | — | — | 20 | μA | V _{DS} = 60V, V _{GS} = 0V |
| | | — | — | 250 | | V _{DS} = 48V, V _{GS} = 0V, T _J = 125°C |
| I _{GSS} | Gate-to-Source Forward Leakage | — | — | 100 | nA | V _{GS} = 20V |
| | Gate-to-Source Reverse Leakage | — | — | -100 | | V _{GS} = -20V |

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

| Symbol | Parameter | Min. | Typ. | Max. | Units | Conditions |
|----------------------------|---|------|------|------|-------|--|
| Q _g | Total Gate Charge | — | 200 | 300 | nC | I _D = 170A |
| Q _{gs} | Gate-to-Source Charge | — | 37 | — | | V _{DS} = 30V |
| Q _{gd} | Gate-to-Drain ("Miller") Charge | — | 60 | — | | V _{GS} = 10V ⑤ |
| Q _{sync} | Total Gate Charge Sync. (Q _g - Q _{gd}) | — | 140 | — | | I _D = 170A, V _{DS} = 0V, V _{GS} = 10V |
| t _{d(on)} | Turn-On Delay Time | — | 16 | — | ns | V _{DD} = 39V |
| t _r | Rise Time | — | 182 | — | | I _D = 170A |
| t _{d(off)} | Turn-Off Delay Time | — | 118 | — | | R _G = 2.7Ω |
| t _f | Fall Time | — | 189 | — | | V _{GS} = 10V ⑤ |
| C _{iss} | Input Capacitance | — | 8970 | — | pF | V _{GS} = 0V |
| C _{oss} | Output Capacitance | — | 1020 | — | | V _{DS} = 50V |
| C _{rss} | Reverse Transfer Capacitance | — | 534 | — | | f = 1.0MHz, See Fig. 5 |
| C _{oss eff. (ER)} | Effective Output Capacitance (Energy Related) | — | 1480 | — | | V _{GS} = 0V, V _{DS} = 0V to 48V ⑦, See Fig. 11 |
| C _{oss eff. (TR)} | Effective Output Capacitance (Time Related) | — | 1920 | — | | V _{GS} = 0V, V _{DS} = 0V to 48V ⑧ |

Diode Characteristics

| Symbol | Parameter | Min. | Typ. | Max. | Units | Conditions |
|------------------|--|--|------|------|-------|---|
| I _S | Continuous Source Current (Body Diode) | — | — | 270① | A | MOSFET symbol showing the integral reverse p-n junction diode. |
| I _{SM} | Pulsed Source Current (Body Diode) ② | — | — | 1080 | A | |
| V _{SD} | Diode Forward Voltage | — | — | 1.3 | V | T _J = 25°C, I _S = 170A, V _{GS} = 0V ⑤ |
| t _{rr} | Reverse Recovery Time | — | 44 | — | ns | T _J = 25°C V _R = 51V, T _J = 125°C I _F = 170A |
| Q _{rr} | Reverse Recovery Charge | — | 63 | — | nC | T _J = 25°C di/dt = 100A/μs ⑤ T _J = 125°C |
| I _{RRM} | Reverse Recovery Current | — | 2.4 | — | A | T _J = 25°C |
| t _{on} | Forward Turn-On Time | Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD) | | | | |

Notes:

- ① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 195A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. (Refer to AN-1140)
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ Limited by T_{Jmax}, starting T_J = 25°C, L = 0.022mH
R_G = 25Ω, I_{AS} = 170A, V_{GS} = 10V. Part not recommended for use above this value .
- ④ I_{SD} ≤ 170A, di/dt ≤ 1360A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 175°C.
- ⑤ Pulse width ≤ 400μs; duty cycle ≤ 2%.
- ⑥ C_{oss eff. (TR)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
- ⑦ C_{oss eff. (ER)} is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.
- ⑨ R_θ is measured at T_J approximately 90°C
- ⑩ R_{θJC} value shown is at time zero

Qualification Information[†]

| | | | |
|-----------------------------------|----------------------|---|------|
| Qualification Level | | Automotive (per AEC-Q101) ^{††} | |
| | | Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level. | |
| Moisture Sensitivity Level | | D ² Pak | MSL1 |
| ESD | Machine Model | Class M4 (+/- 800V) ^{†††} AEC-Q101-002 | |
| | Human Body Model | Class H3A (+/- 6000V) ^{†††} AEC-Q101-001 | |
| | Charged Device Model | Class C5 (+/- 2000V) ^{†††} AEC-Q101-005 | |
| RoHS Compliant | | Yes | |

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage.

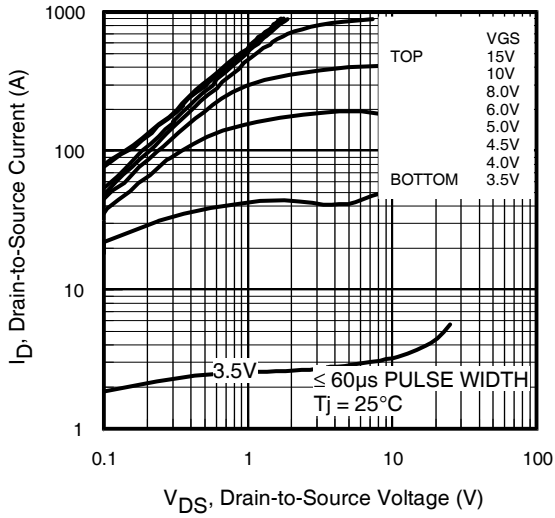


Fig 1. Typical Output Characteristics

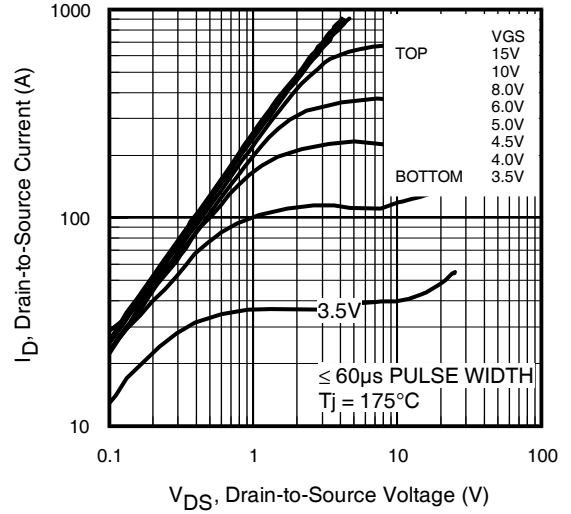


Fig 2. Typical Output Characteristics

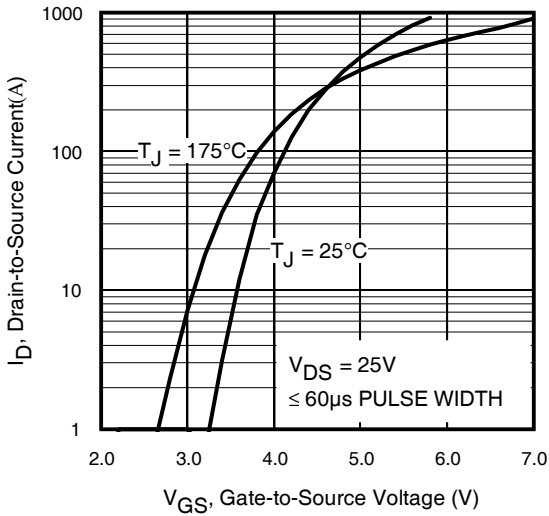


Fig 3. Typical Transfer Characteristics

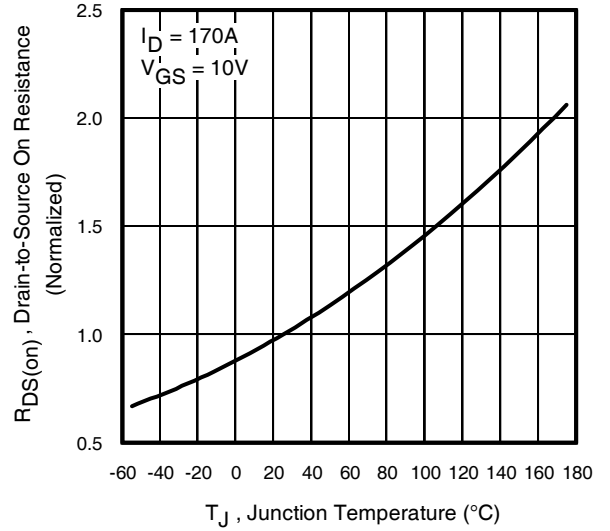


Fig 4. Normalized On-Resistance vs. Temperature

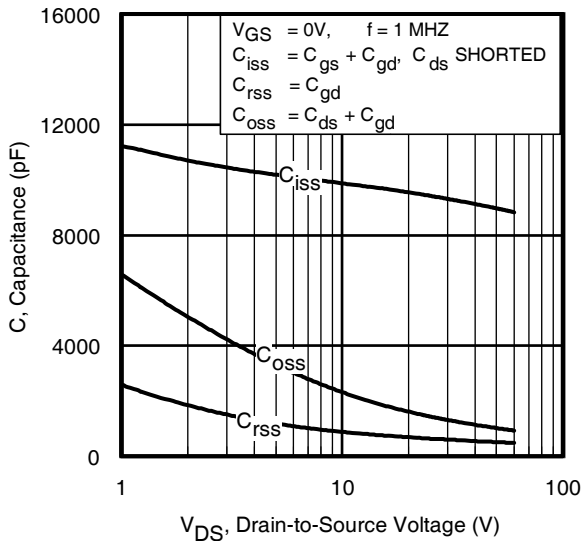


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

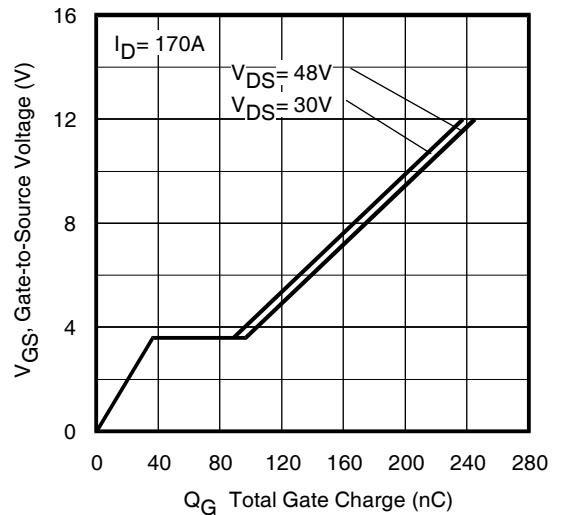


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

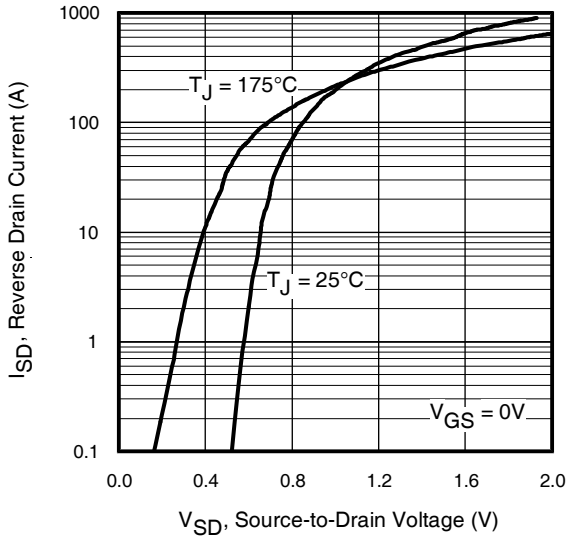


Fig 7. Typical Source-Drain Diode Forward Voltage

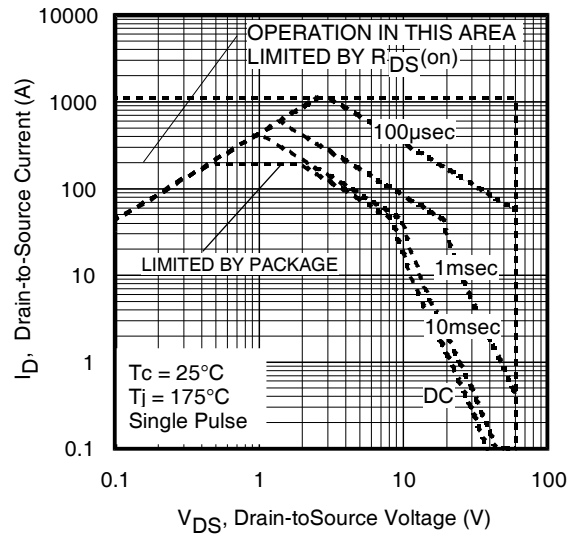


Fig 8. Maximum Safe Operating Area

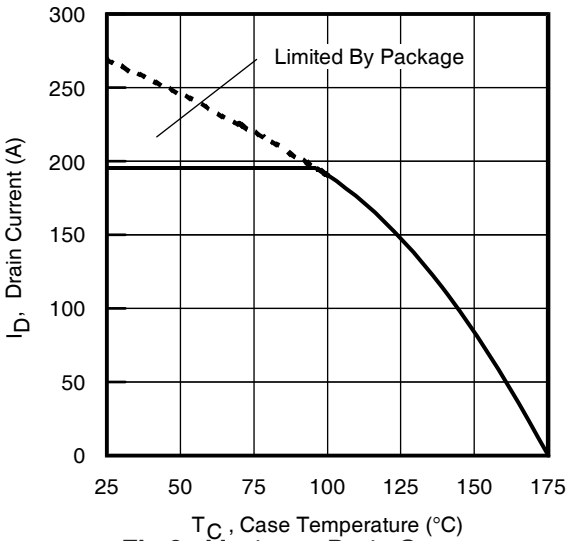


Fig 9. Maximum Drain Current vs. Case Temperature

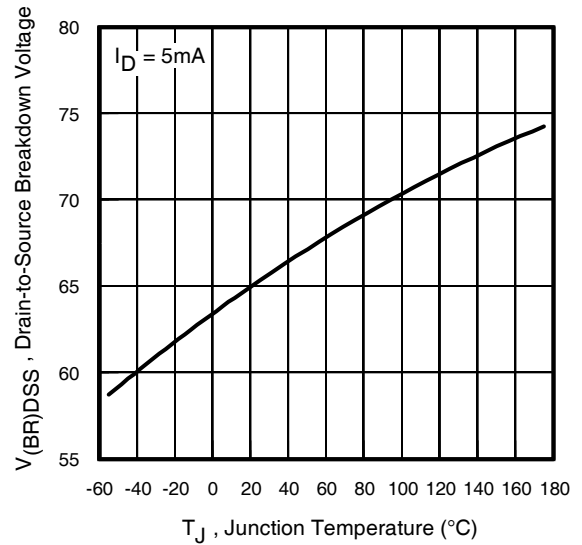


Fig 10. Drain-to-Source Breakdown Voltage

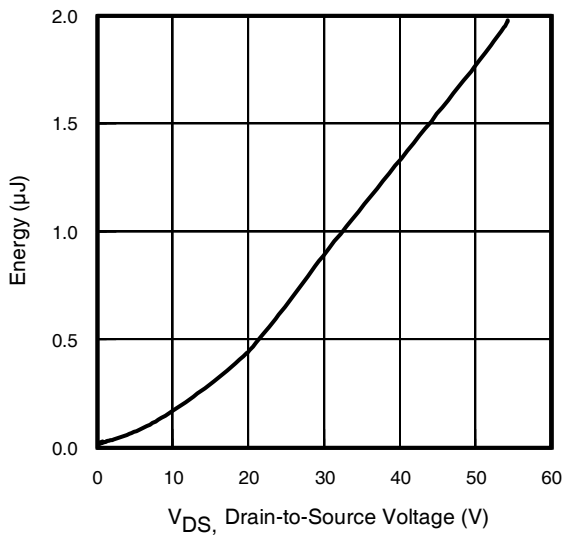


Fig 11. Typical C_{OSS} Stored Energy

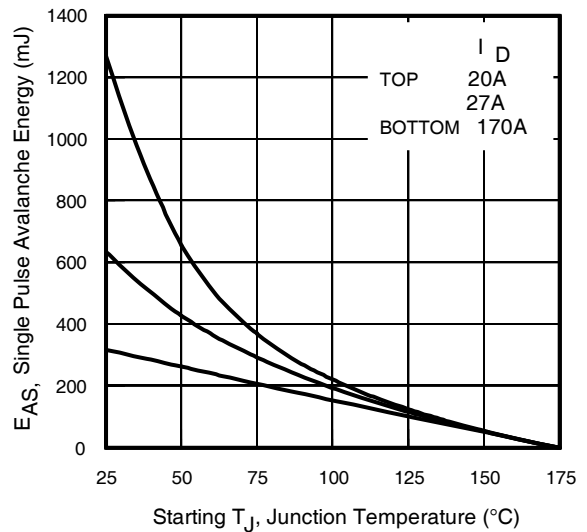


Fig 12. Maximum Avalanche Energy Vs. Drain Current

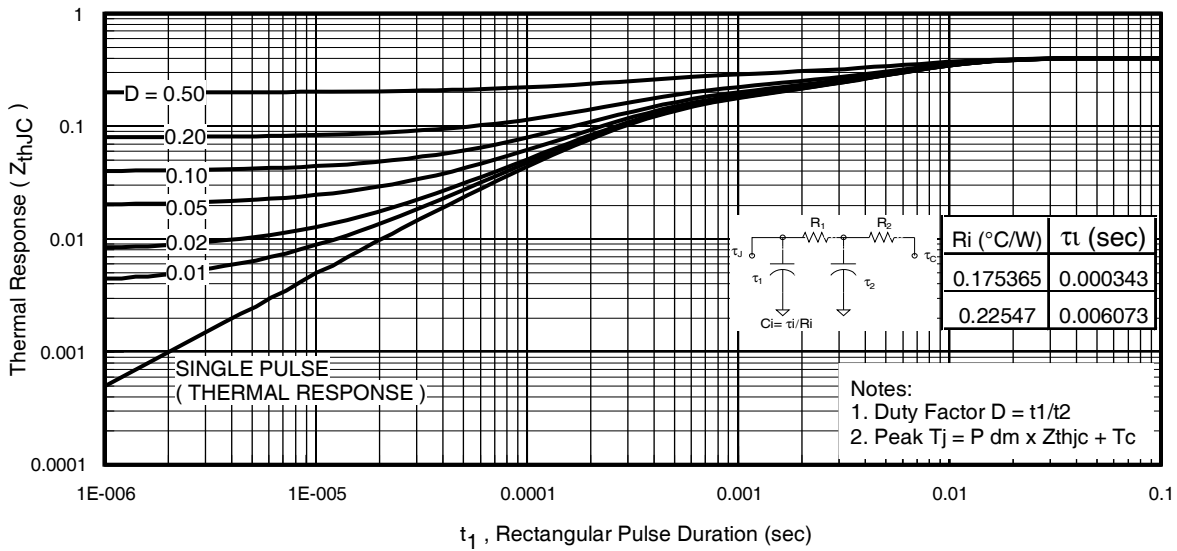


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

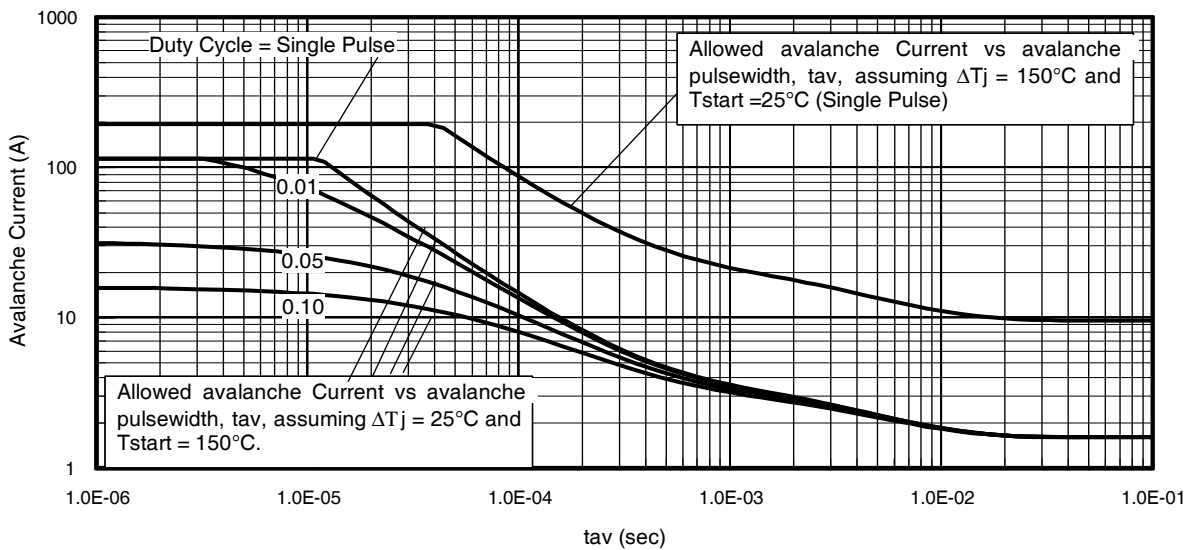
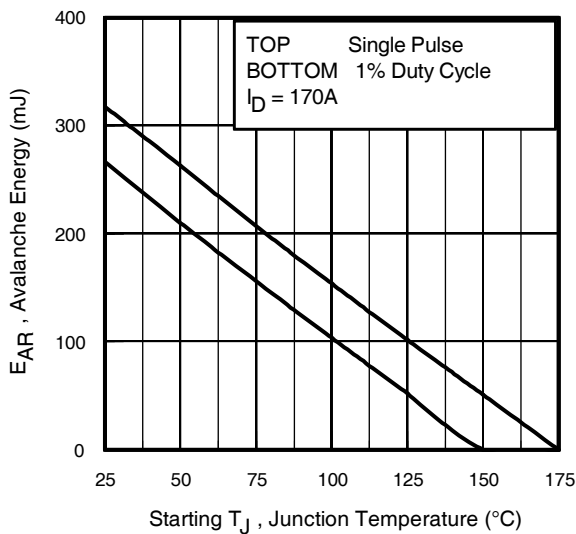


Fig 14. Typical Avalanche Current vs. Pulsewidth



Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 16a, 16b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 14, 15).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

Fig 15. Maximum Avalanche Energy vs. Temperature

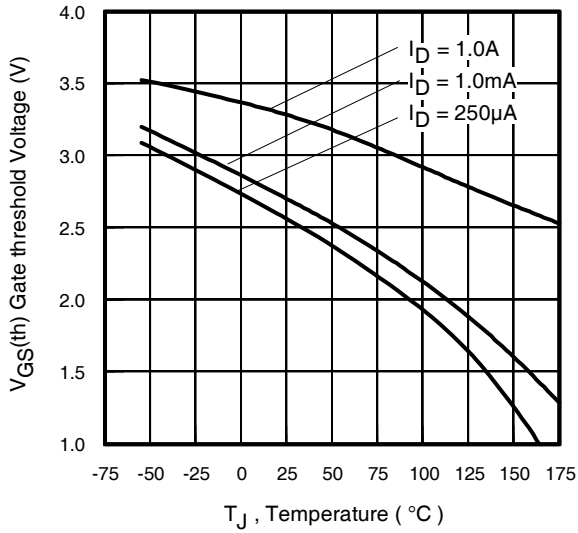


Fig 16. Threshold Voltage Vs. Temperature

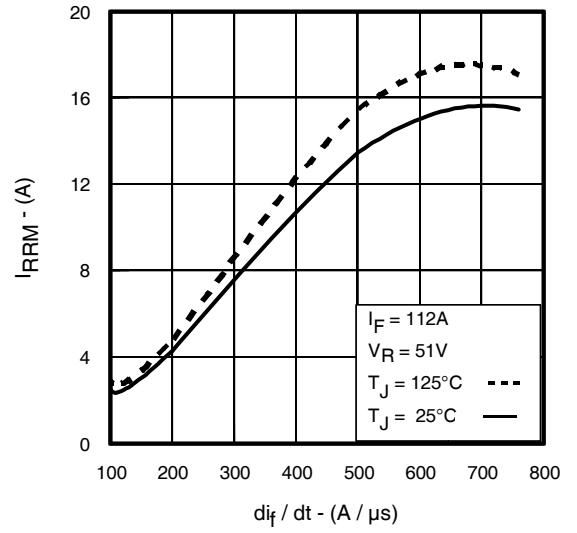


Fig. 17 - Typical Recovery Current vs. di_f/dt

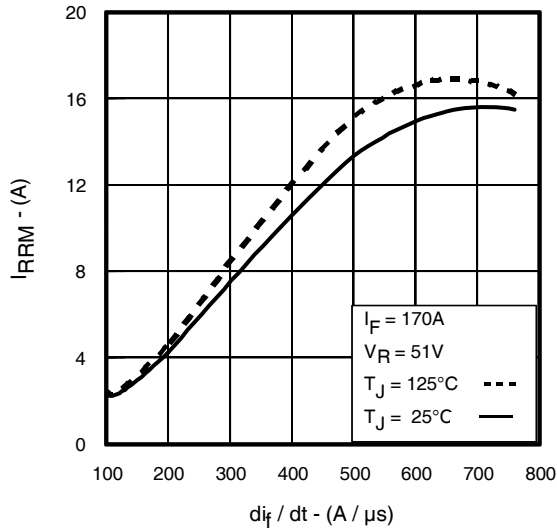


Fig. 18 - Typical Recovery Current vs. di_f/dt

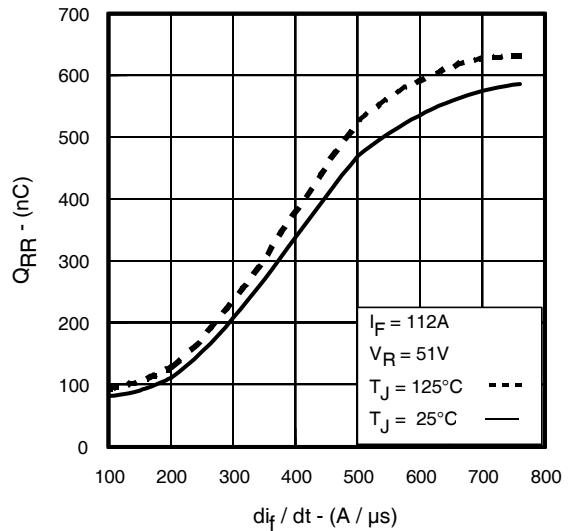


Fig. 19 - Typical Stored Charge vs. di_f/dt

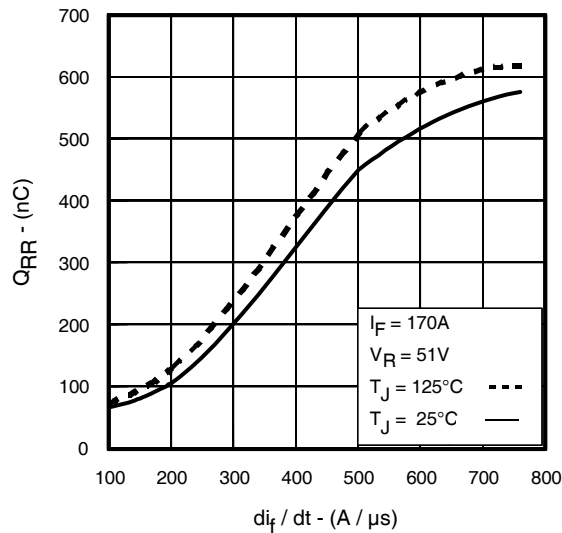
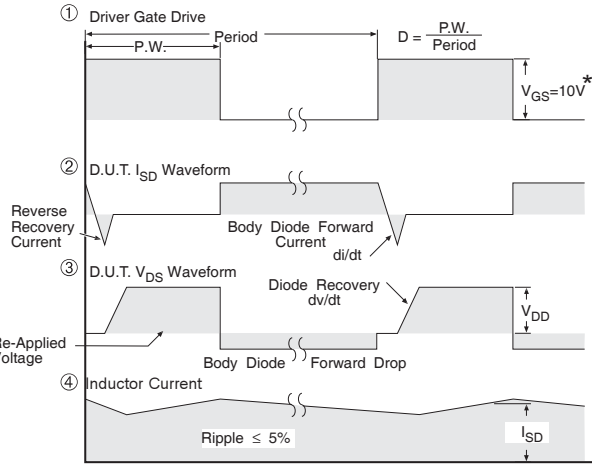
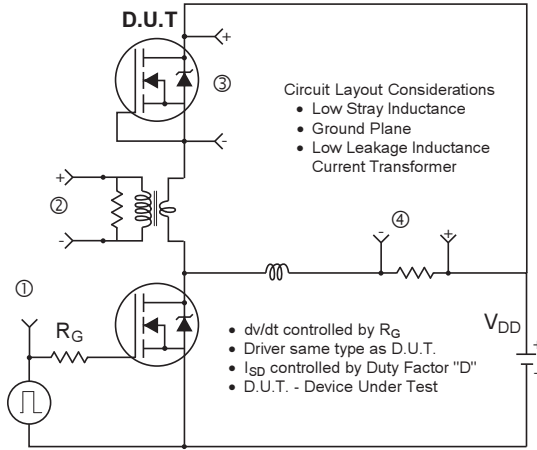


Fig. 20 - Typical Stored Charge vs. di_f/dt



* $V_{GS} = 5V$ for Logic Level Devices

Fig 21. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

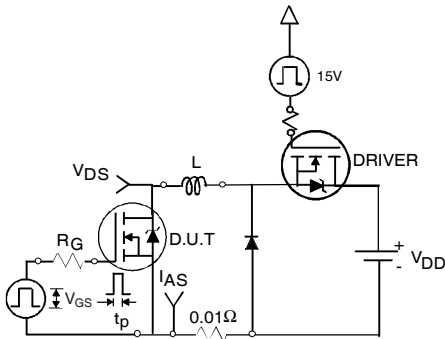


Fig 22a. Unclamped Inductive Test Circuit



Fig 22b. Unclamped Inductive Waveforms

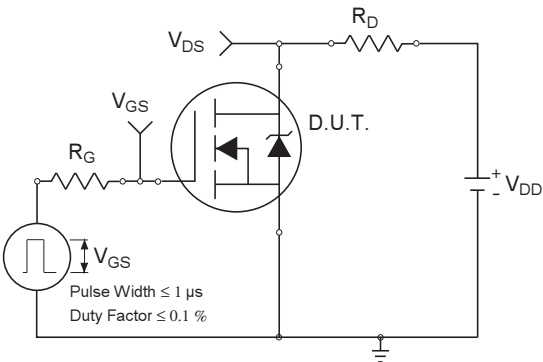


Fig 23a. Switching Time Test Circuit

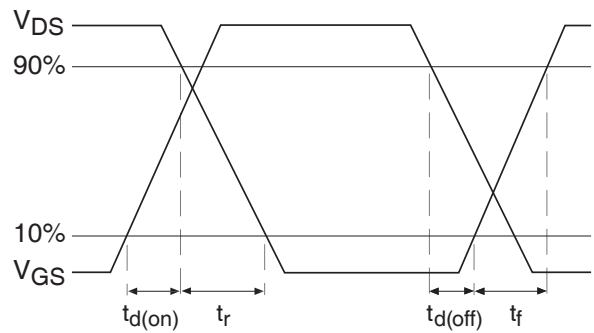


Fig 23b. Switching Time Waveforms

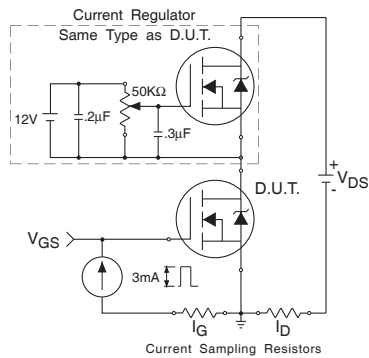


Fig 24a. Gate Charge Test Circuit

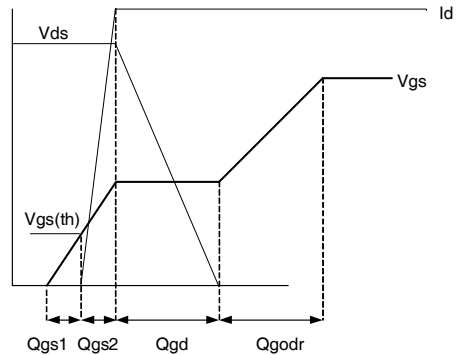
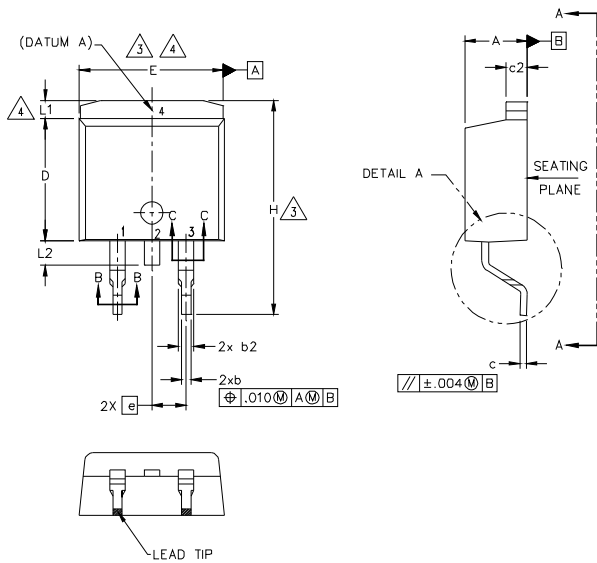


Fig 24b. Gate Charge Waveform

D²Pak Package Outline (Dimensions are shown in millimeters (inches))



| SYMBOL | DIMENSIONS | | | | NOTES |
|--------|-------------|-------|----------|------|-------|
| | MILLIMETERS | | INCHES | | |
| | MIN. | MAX. | MIN. | MAX. | |
| A | 4.06 | 4.83 | .160 | .190 | 5 |
| A1 | 0.00 | 0.254 | .000 | .010 | |
| b | 0.51 | 0.99 | .020 | .039 | |
| b1 | 0.51 | 0.89 | .020 | .035 | |
| b2 | 1.14 | 1.78 | .045 | .070 | |
| b3 | 1.14 | 1.73 | .045 | .068 | |
| c | 0.38 | 0.74 | .015 | .029 | |
| c1 | 0.38 | 0.58 | .015 | .023 | |
| c2 | 1.14 | 1.65 | .045 | .065 | |
| D | 8.38 | 9.65 | .330 | .380 | |
| D1 | 6.86 | - | .270 | - | |
| E | 9.65 | 10.67 | .380 | .420 | |
| E1 | 6.22 | - | .245 | - | |
| e | 2.54 BSC | | .100 BSC | | |
| H | 14.61 | 15.88 | .575 | .625 | 4 |
| L | 1.78 | 2.79 | .070 | .110 | |
| L1 | - | 1.65 | - | .066 | |
| L2 | 1.27 | 1.78 | - | .070 | |
| L3 | 0.25 BSC | | .010 BSC | | |
| L4 | 4.78 | 5.28 | .188 | .208 | |

LEAD ASSIGNMENTS

DIODES

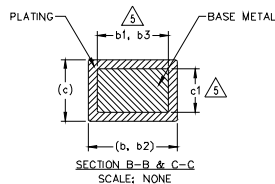
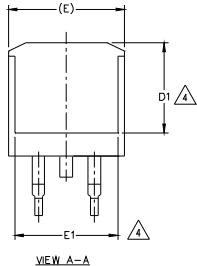
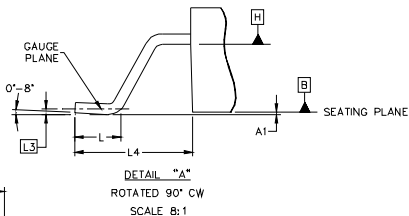
- 1.- ANODE (TWO DIE) / OPEN (ONE DIE)
- 2, 4.- CATHODE
- 3.- ANODE

HEXFET

- 1.- GATE
- 2, 4.- DRAIN
- 3.- SOURCE

IGBTs, CoPACK

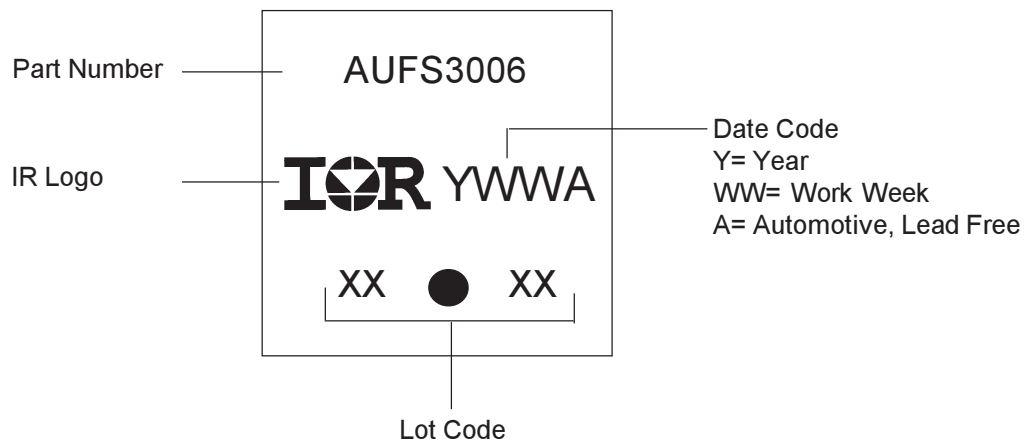
- 1.- GATE
- 2, 4.- COLLECTOR
- 3.- EMITTER



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

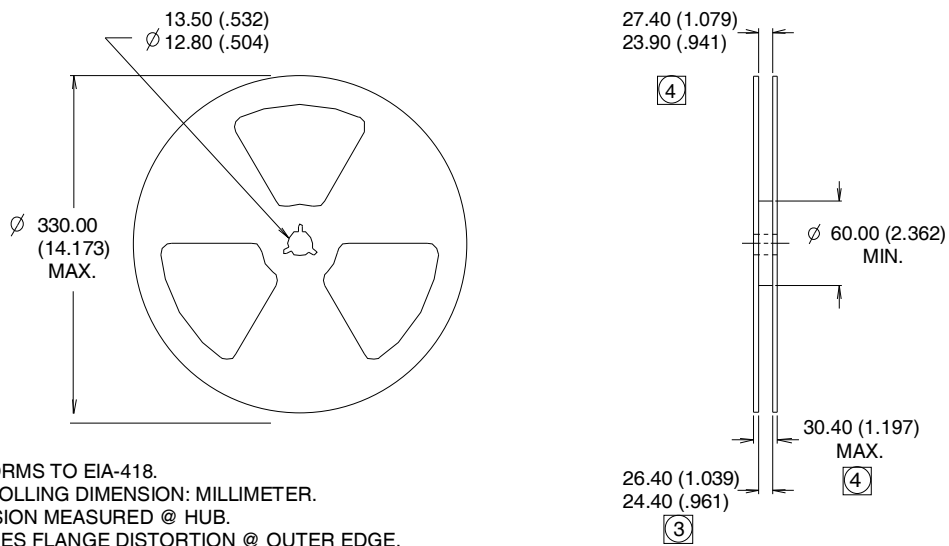
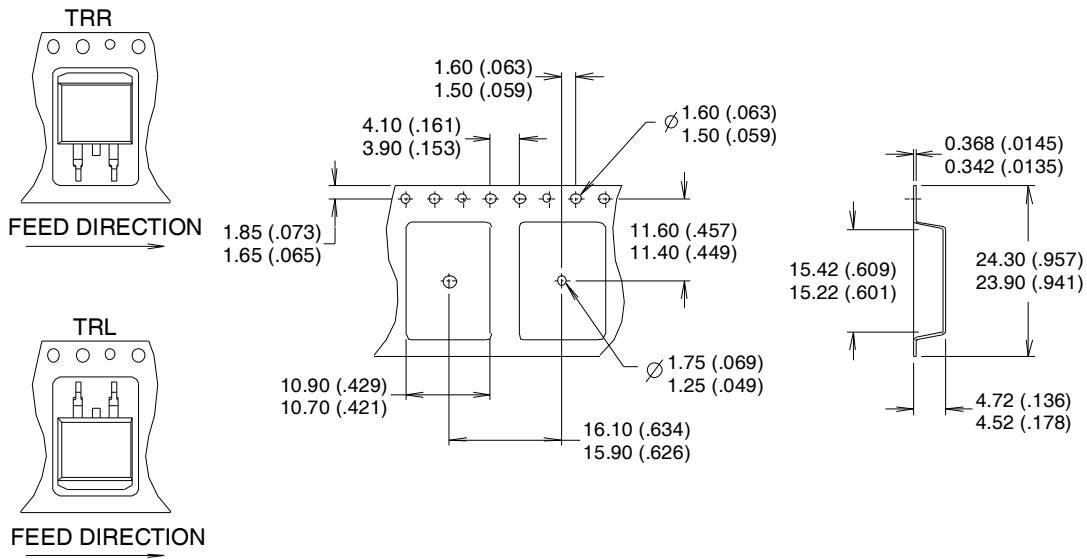
D²Pak Part Marking Information



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

D²Pak (TO-263AB) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. COMFORMS TO EIA-418.
 2. CONTROLLING DIMENSION: MILLIMETER.
 - ③ DIMENSION MEASURED @ HUB.
 - ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Ordering Information

| Base part number | Package Type | Standard Pack | | Complete Part Number |
|------------------|--------------|---------------------|----------|----------------------|
| | | Form | Quantity | |
| AUIRFS3006 | D2Pak | Tube | 50 | AUIRFS3006 |
| | | Tape and Reel Left | 800 | AUIRFS3006TRL |
| | | Tape and Reel Right | 800 | AUIRFS3006TRR |

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